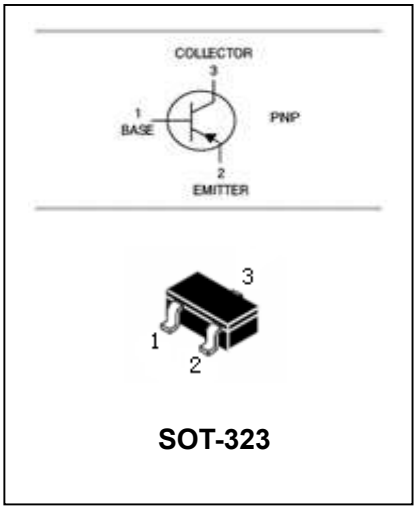
PNP Silicon Epitaxial Planar Transistor 2SA1576A

FEATURES

- Power dissipation.(P_C=200mW)
- Excellent H_{FE} Linearity.
- Complements the 2SC4081.

Lead-free



SOT-323

APPLICATIONS

- General purpose application.
- Switching and amplification.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1576A	FQ/FR/FS	SOT-323

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	**Parameter**	**Value**	**Units**
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-150	mA
P_C	Collector Dissipation	200	mW
T_{stg}	Storage Temperature	-55 to +150	℃
$T_{j,}$	Junction Temperature	150	℃

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ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	**Symbol**	**Test conditions**	**MIN**	**TYP**	**MAX**	**UNIT**
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-50μA,I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-50μA,I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}=-60V,I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-6V,I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-6V,I_C=-1mA	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-50mA, I_B=-5mA			-0.5	V
Transition frequency	f_T	V_{CE}=-12V, I_C= -2mA f=30MHz	140			MHz
Collector output capacitance	C_{ob}	V_{CB}=-12V,I_E=0,f=1MHz		4	5	pF

CLASSIFICANTION OF h_{FE}

Rank	**Q**	**R**	**S**
Range	120-270	180-390	270-560
marking	FQ	FR	FS

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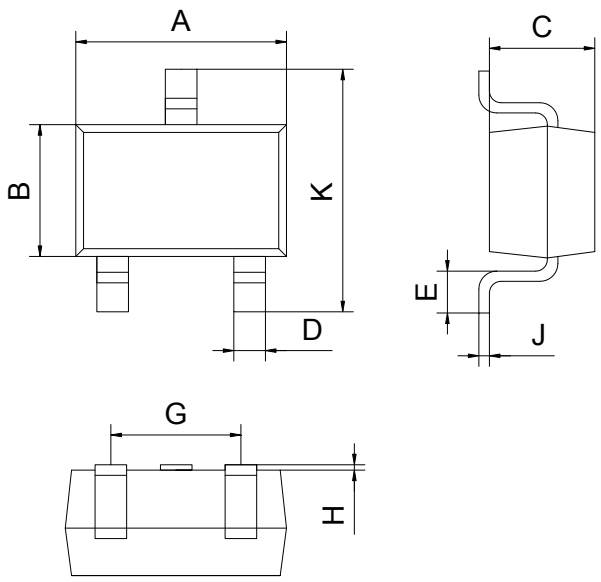
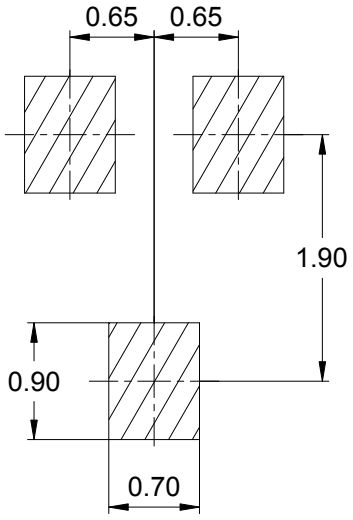
PACKAGE OUTLINE

Plastic surface mounted package SOT-323



SOT-323		
Dim	Min	Max
A	2.00	2.20
B	1.15	1.35
C	0.95 Typical	
D	0.30 Typical	
E	0.25	0.40
G	1.2	1.4
H	0.02	0.10
J	0.10 Typical	
K	2.20	2.40
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
2SA1576A	SOT-323	3000/Tape&Reel